

Supporting Information

Exploring the Sodium Ion Storage Mechanism of Gallium Sulfide (Ga_2S_3): A Combined Experimental and Theoretical Approach

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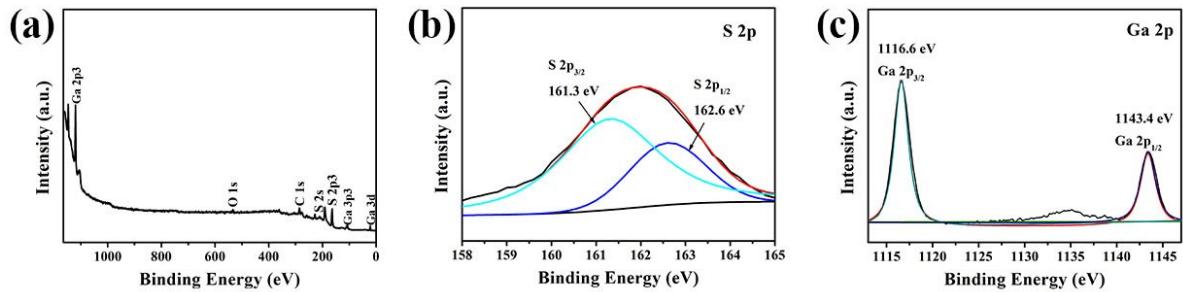


Figure. S1. The full-scan spectra in (a) show the presence of the Ga 2p and S 2p peaks; The Ga 2p and S 2p core levels were scanned respectively. As presented in (b) the fitting of S 2p spectra; (c) the fitting of Ga 2p spectra.

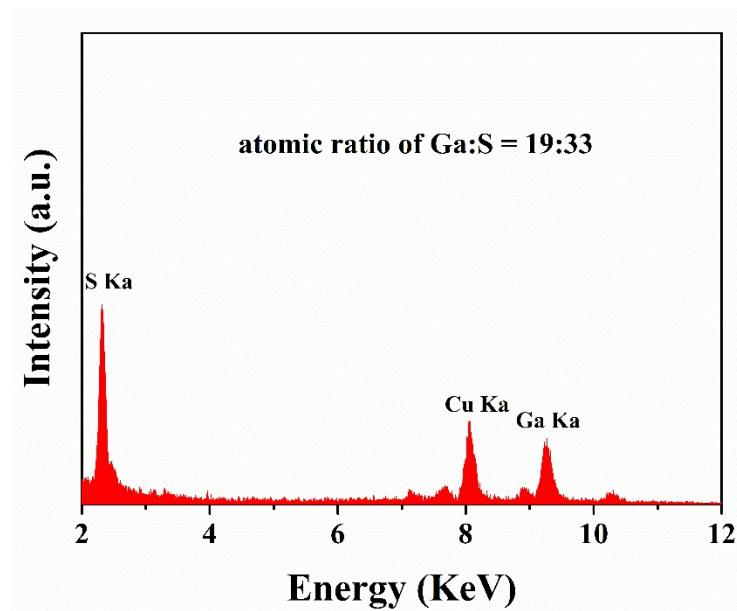


Figure. S2. EDS spectra of as-synthesized Ga_2S_3

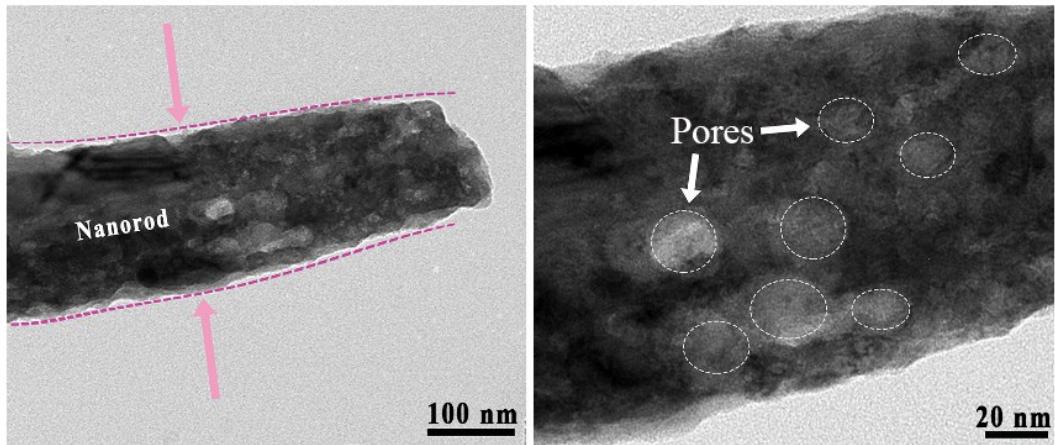


Figure. S3. Typical TEM images of Ga₂S₃ rods to show porous structure inside.

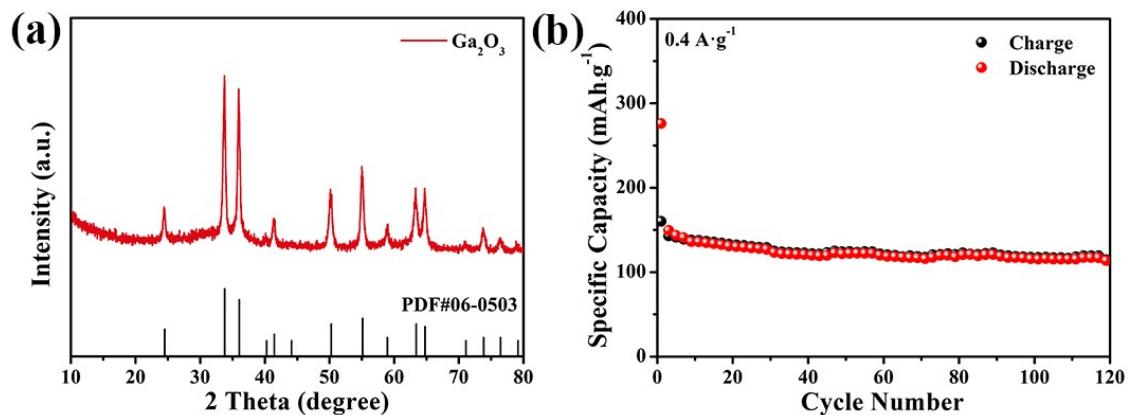


Figure. S4. (a) XRD patterns of Ga₂O₃; (b) cycling performance of Ga₂O₃ at the current density of 0.4 A g⁻¹.

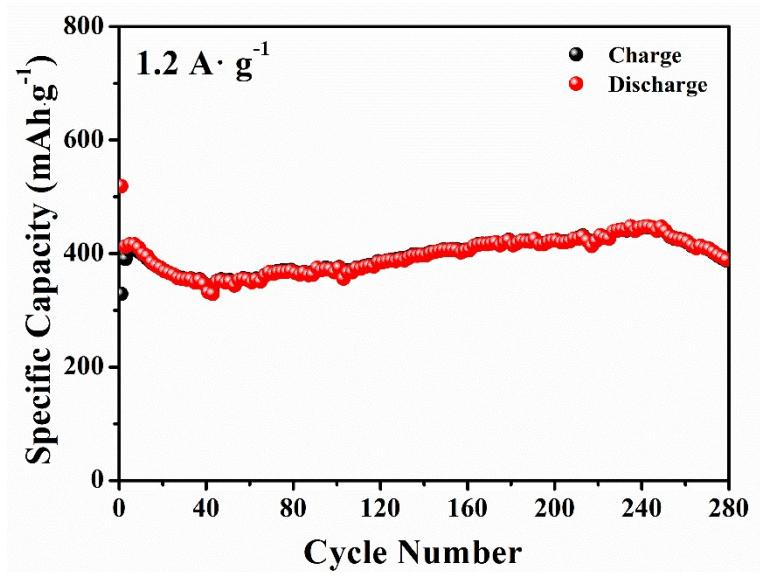


Figure. S5. Long cycling performance of Ga_2S_3 at the current density of 1.2 A g^{-1} .

Table. S1. Comparison of the characteristic parameters of different sulfide-based electrodes for SIBs applications.

Anode materials	Cycle number	Current	Cycling capacity	Ref
Bimetallic sulfide hollow nanocubes	150	500 mA g ⁻¹	87 mAh g ⁻¹	1
FeS microspheres	45	200 mA g ⁻¹	500 mAh g ⁻¹	2
Co _{1-x} S/C nanoparticles	130	1000 mA g ⁻¹	320 mAh g ⁻¹	3
Co ₉ S ₈ quantum dots	500	300 mA g ⁻¹	628 mAh g ⁻¹	4
CoS _x quantum dots	200	1000 mA g ⁻¹	414 mAh g ⁻¹	5
CoS ₂ nanoparticles	1000	1000 mA g ⁻¹	315 mAh g ⁻¹	6
CoS ₂ /rGO composite	100	100 mA g ⁻¹	400 mAh g ⁻¹	7
CoS ₂ /carbon composite	60	500 mA g ⁻¹	330 mAh g ⁻¹	8
M-CoS@C	100	200 mA g ⁻¹	532 mAh g ⁻¹	9
CoS/rGO	30	100 mA g ⁻¹	426 mAh g ⁻¹	10
CuS nanodisks	100	100 mA g ⁻¹	350 mAh g ⁻¹	11
FeS@Fe ₃ C@graphitic carbon	100	200 mA g ⁻¹	575 mAh g ⁻¹	12

$\text{MoS}_2/\text{Co}_9\text{S}_8/\text{C}$ nanoboxes	100	500 mA g^{-1}	546 mAh g^{-1}	13
SnS@C nanotubes	100	200 mA g^{-1}	426 mAh g^{-1}	14
MoS_2 nanoflakes	100	100 mA g^{-1}	474 mAh g^{-1}	15
NiS/carbon composites	100	200 mA g^{-1}	483 mAh g^{-1}	16
$\text{Sn@Sb}_2\text{S}_3/\text{rGO}$	60	200 mA g^{-1}	600 mAh g^{-1}	17
$\text{Sb}_2\text{S}_3/\text{C}$	100	200 mA g^{-1}	545 mAh g^{-1}	18
SnS	50	100 mA g^{-1}	410 mAh g^{-1}	19
$\text{SnS}_2@\text{rGO}$	100	50 mA g^{-1}	509 mAh g^{-1}	20
$\text{SnS}_2/\text{S}/\text{rGO}$	80	100 mA g^{-1}	450 mAh g^{-1}	21
SnS/CNS	100	1000 mA g^{-1}	474 mAh g^{-1}	22
VS_2 microflowers	150	200 mA g^{-1}	330 mAh g^{-1}	23
$\text{VS}_4@\text{GS}$ nanocomposites	200	500 mA g^{-1}	250 mAh g^{-1}	24
ZnS@C	100	100 mA g^{-1}	768 mAh g^{-1}	25
ZnS quantum dots	100	100 mA g^{-1}	759 mAh g^{-1}	26
$(\text{Co}_{1/3}\text{Fe}_{2/3})\text{Se}_2$	60	300 mA g^{-1}	594 mAh g^{-1}	27

NiSe ₂ /C porous nanofiber	100	200 mA g ⁻¹	468 mAh g ⁻¹	28
NiSe ₂ /rGO	1000	1000 mA g ⁻¹	346 mAh g ⁻¹	29
Nickel-doped Co ₉ S ₈ hollow nanoparticles	200	2000 mA g ⁻¹	355 mAh g ⁻¹	30
Co ₉ Se ₈ /rGO nanocomposites	100	50 mA g ⁻¹	406 mAh g ⁻¹	31
Bi _{0.25} Sb _{1.75} Te ₃	100	200 mA g ⁻¹	406 mAh g ⁻¹	32
Fe _{1-x} S@Na _{2.9} PS _{3.95} Se _{0.05}	100	100 mA g ⁻¹	494.3 mAh g ⁻¹	33
CoSe ₂ /(NiCo)Se ₂ box-in-box hollow nanocubes	80	200 mA g ⁻¹	497 mAh g ⁻¹	34
CoSe _x -rGO	50	300 mA g ⁻¹	420 mAh g ⁻¹	35
CoSe _x	50	300 mA g ⁻¹	215 mAh g ⁻¹	35
Fe ₇ Se ₈ @NC nanoparticles	1200	100 mA g ⁻¹	339 mAh g ⁻¹	36
FeS _{2-x} Se _x	6000	2000 mA g ⁻¹	220 mAh g ⁻¹	37
FeTe ₂ -rGO	80	200 mA g ⁻¹	293 mAh g ⁻¹	38
Mo ₆ T ₈ (T = S, Se)	50	20 mA g ⁻¹	60.3 mAh g ⁻¹	39
MoSe ₂ /C	100	500/1000 mA g ⁻¹	423/395 mAh g ⁻¹	40
MoSe ₂ grown on N,P-co-doped carbon nanosheets	1000	500 mA g ⁻¹	378 mAh g ⁻¹	41

MoSe₂	120	100/1000 mA g ⁻¹	543/491 mAh g ⁻¹	42
Fe_{0.3}Nb_{0.7}S_{1.6}Se_{0.4} Nanosheets	750	1000 mA g ⁻¹	250 mAh g ⁻¹	43
RGO/Ni₃S₂/Ni	100	/	433 mAh g ⁻¹	44
Ni₃Se₂	100	500 mA g ⁻¹	339.7 mAh g ⁻¹	45
Ni_{0.85}Se/C hollow nanowires	100	0.2C	390 mAh g ⁻¹	46
Nitrogen-doped CoSe/C	50	500 mA g ⁻¹	531.6 mAh g ⁻¹	47
N-Doped Graphene@Sb₂Se₃	50	100 mA g ⁻¹	548.6 mAh g ⁻¹	48
Sb₂Se₃/rGO	500	1000 mA g ⁻¹	417 mAh g ⁻¹	49
Sb₂Te₃/C	400	1000 mA g ⁻¹	360 mAh g ⁻¹	50
SnSe NSCs nanosheet clusters	100	200/2000/5000 mA g ⁻¹	271/183/70 mAh g ⁻¹	51
SnSe nanoplates	50	300 mA g ⁻¹	558 mAh g ⁻¹	52
SnTe/C	100	50 mA g ⁻¹	316 mAh g ⁻¹	53
Sb₂Te₃@RGO	80	100 mA g ⁻¹	514 mAh g ⁻¹	54
Nano Te@C	1000	60 mA g ⁻¹	345 mAh g ⁻¹	55
Ga₂S₃	100	400 mA g⁻¹	476 mAh g⁻¹	this work

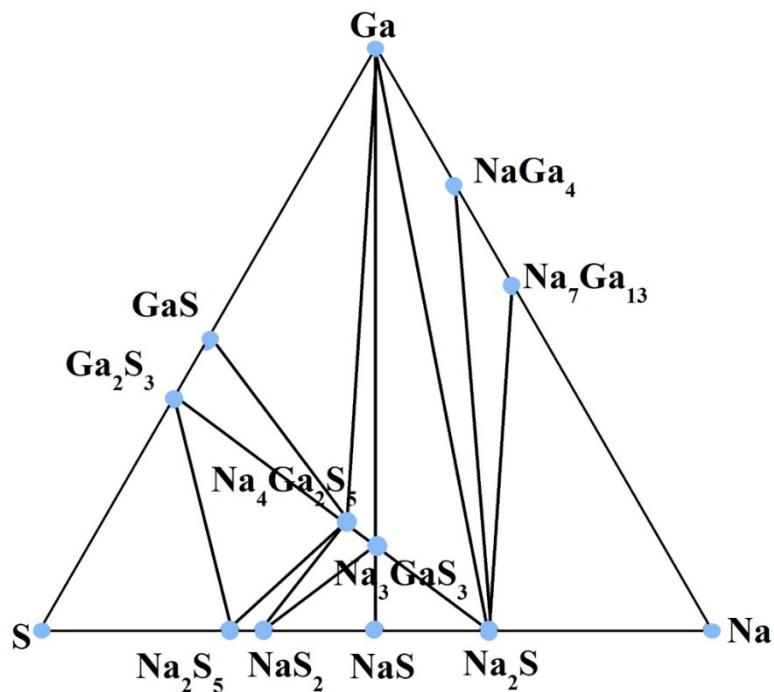


Figure. S6. The phase diagram presents all the thermodynamically stable phases in the Ga-S-Na chemical system (blue dots)

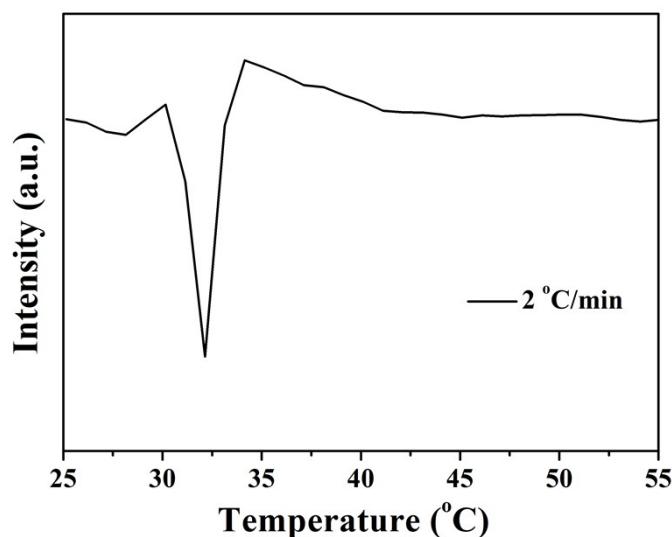


Figure S7. DSC traces ($2^{\circ}/\text{min}$, Ar flow) for electrodes discharged at 0.5 V

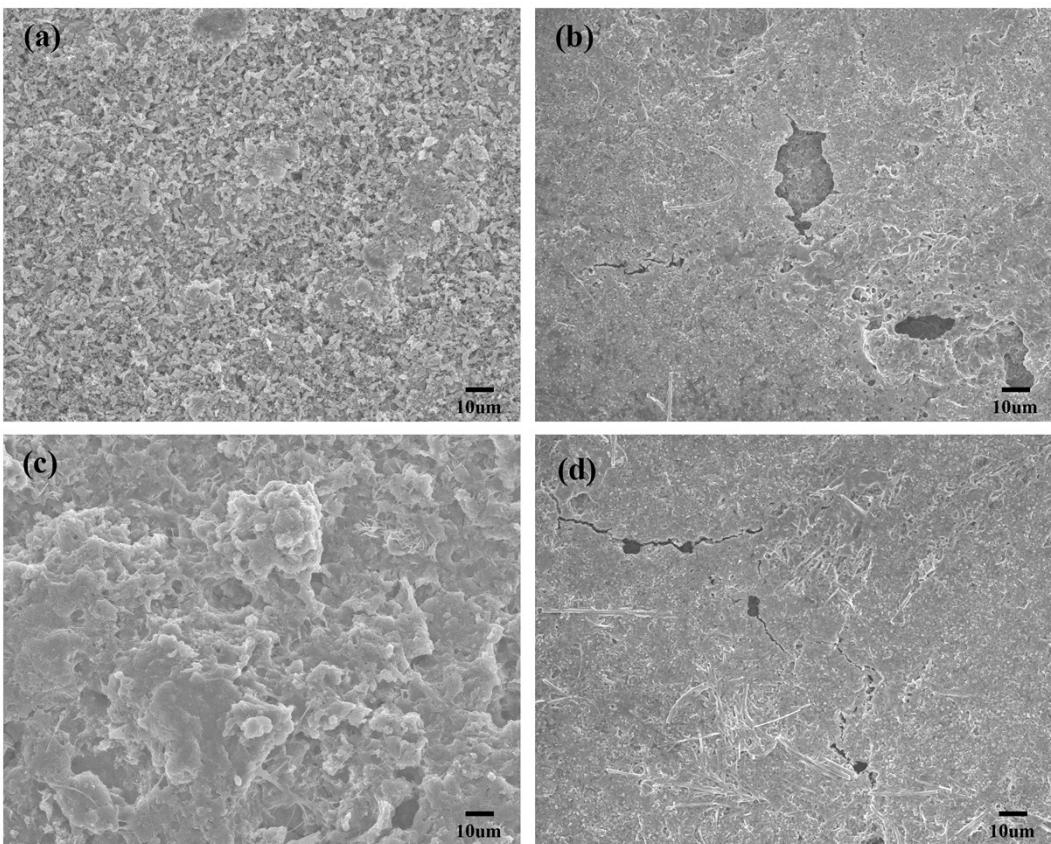
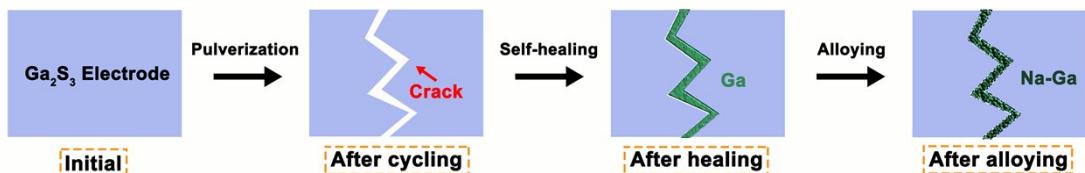


Figure S8. SEM observation of Ga_2S_3 electrode during the discharge: (a) initial state; discharged at (b) 0.7 V (c) 0.4 V and (d) 0.01 V.



Schematic R1. Illustrate the self-healing process of Ga-based material upon discharge.

Assemble of K Ion Battery. To prepare working electrodes, active material, graphene and binder (polyvinylidene fluoride, PVdF) were mixed in a weight ratio of 70:20:10; 1-methyl-2-pyrrolidinone solvent (Aldrich, 99%) was added to form slurry. The well-mixed slurry was coated onto a Cu foil as a current collector using a doctor blade method and then dried under vacuum at 80 °C overnight. Coin-type half-cells were assembled inside an argon-filled glove box (<0.1 ppm, H₂O and O₂), using the metallic potassium foil as the counter electrode, the Whatman glass fiber as the separator and 0.5 L mol⁻¹ CF₃SO₃K solution in diethylene glycol dimethyl ether as the electrolyte. The charge-discharge cycling was performed within the voltage range of 0.01–3.00 V vs. K/K⁺ on a battery test instrument (CT2001A, LAND).

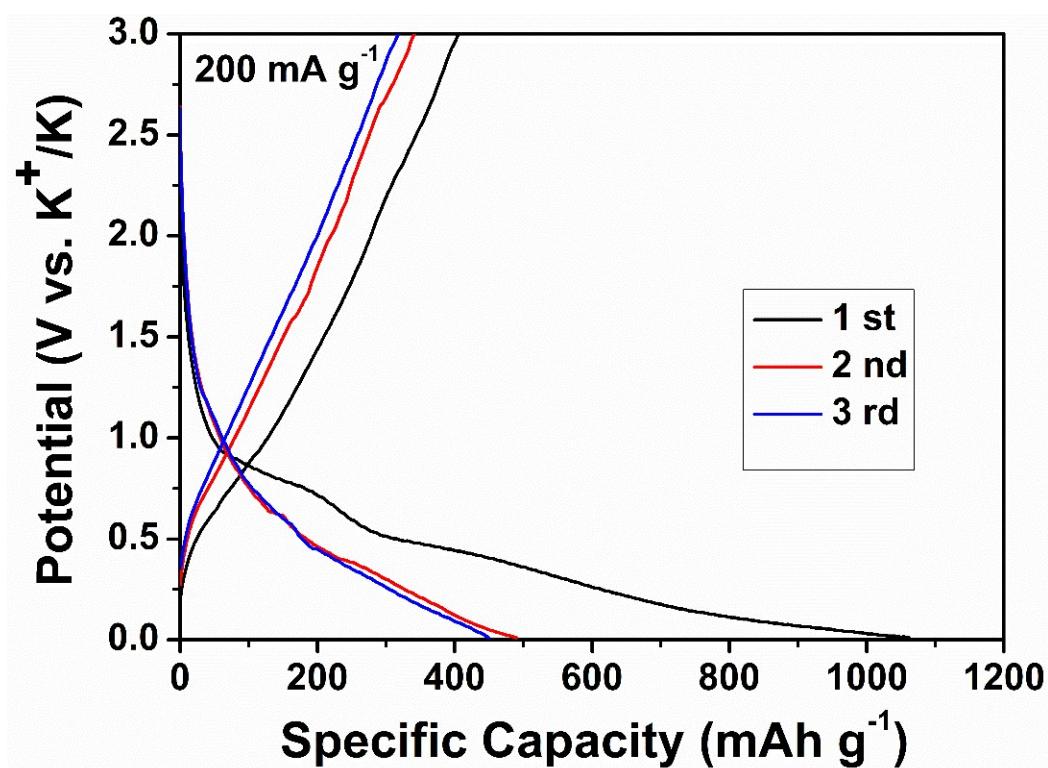


Figure S9. Galvanostatic charge-discharge voltage profiles of the Ga_2S_3 for K ion battery

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